SIMICONDUCTOR DEVICE WITH DECOUPLING CAPACITANCE AND METHOD THEREOF

ABSTRACT

A semiconductor device is disclosed that provides a decoupling capacitance and method for the same. The semiconductor device includes a first circuit region having a first device layer (24) over an isolation layer (20) and a second circuit region adjacent the first circuit region having a second device layer over a well. An implant layer (25) is implanted beneath the isolation layer (20) in the first circuit region, which will connect to the well of the second circuit region.

Fig.1